

HRW0302A

Silicon Schottky Barrier Diode for Rectifying

REJ03G0156-0800Z

(Previous: ADE-208-015G)

Rev.8.00 Dec.15.2003

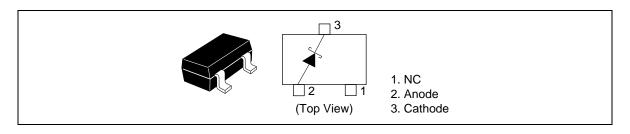
Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRW0302A	S11	MPAK

Pin Arrangement



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit	
Repetitive peak reverse voltage	V _{RMM} *1	20	V	
Average rectified current	l ₀ *1	300	mA	
Non-Repetitive peak forward surge current	I _{FSM} *2	3	А	
Junction temperature	Tj	125	°C	
Storage temperature	Tstg	-55 to +125	°C	

Notes: 1. See from Fig.4 to Fig.6

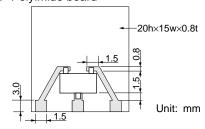
2. 10ms sine wave 1 pulse

Electrical Characteristics

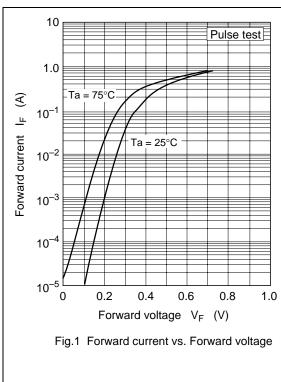
 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V _F	_	_	0.40	V	I _F = 300 mA
Reverse current	I_R	_	_	100	μА	V _R = 20 V
Capacitance	С	_	_	100	pF	V _R = 0 V, f = 1 MHz
Thermal resistance	R _{th(j-a)}	_	340	_	°C/W	Polyimide board *1

Note: 1. Polyimide board



Main Characteristic



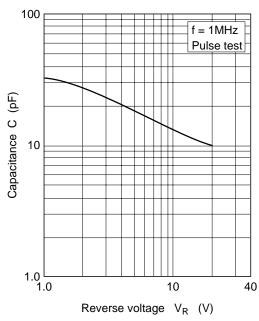


Fig.3 Capacitance vs. Reverse voltage

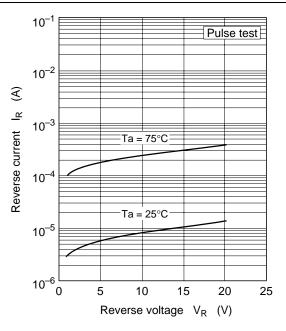


Fig.2 Reverse current vs. Reverse voltage

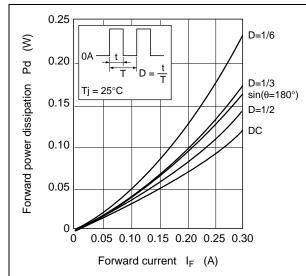


Fig.4 Forward power dissipation vs. Forward current

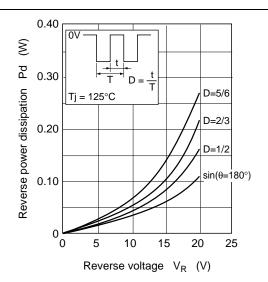
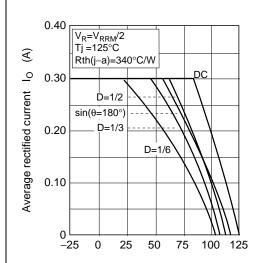


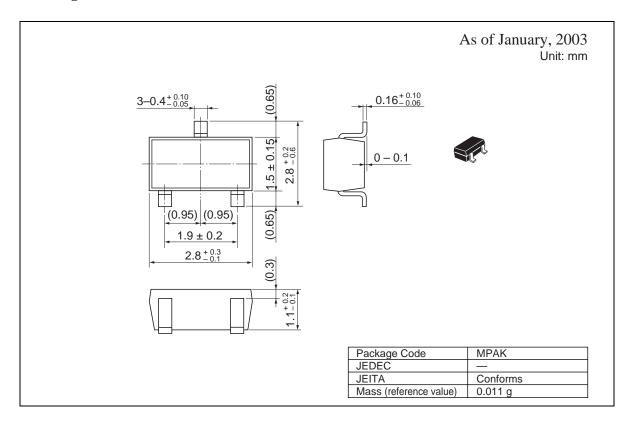
Fig.5 Reverse power dissipation vs. Reverse voltage



Ambient temperature Ta (°C)

Fig.6 Average rectified current vs. Ambient temperature

Package Dimensions



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